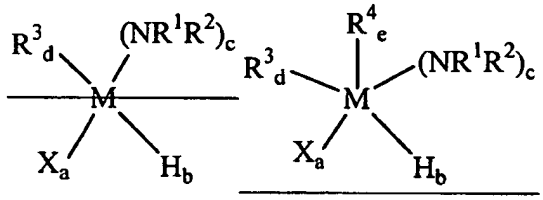
hydride elimination. Thus, preferred bulky groups contain a hydrogen bonded to the carbon in the beta position to the germanium. --

Please delete the paragraph beginning with "Accordingly, the present . . ." at page 14, line 9, and replace it with the following new paragraph: SB 4-30-08

-- Accordingly, the present invention provides a device for feeding a fluid stream saturated with an organometallic compound suitable for depositing a metal film containing silicon, germanium, and combinations thereof to a chemical vapor deposition system including a vessel having an elongated cylindrical shaped portion having an inner surface having a cross-section, a top closure portion and a bottom closure portion, the top closure portion having an inlet opening for the introduction of a carrier gas and an outlet opening, the elongated cylindrical shaped portion having a chamber containing one or more organometallic compounds of formula I



(I)

wherein M is Si or Ge; R^1 and R^2 are independently chosen from H, alkyl, alkenyl, alkynyl and aryl; each R^3 is independently chosen from $(C_1\text{-}C_{12})$alkyl, alkenyl, alkynyl and aryl, provided that R^3 is not cyclopentadienyl; each R^4 is independently chosen from $(C_3\text{-}C_{12})$alkyl; X is halogen; a = 0-3; b = 0-3; c = 0-3; d = 0-2; e = 0-4; and a + b + c + d + e = 4; wherein $R^3 \neq R^4$; wherein the sums of a + b and a + d are each ≤ 3; provided that when M = Si the sum of b + c is ≤ 3; the inlet opening being in fluid communication with the chamber and the chamber being in fluid communication with the outlet opening. --